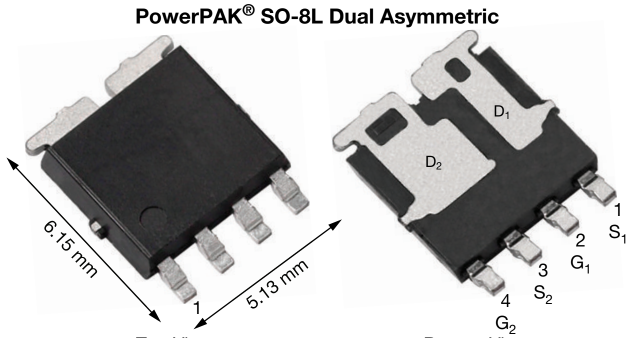
Automotive Dual N-Channel 60 V (D-S) 175 °C MOSFETs

PowerPAK® SO-8L Dual Asymmetric

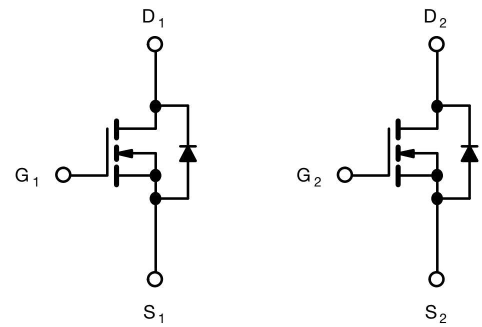


Top View   Bottom View

FEATURESS

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_g and UIS tested
- Optimized for synchronous buck applications
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

AUTOMOTIVE GRADE
Pb-free
RoHS COMPLIANT
HALOGEN FREE



N-Channel 1 MOSFET   N-Channel 2 MOSFET

PRODUCT SUMMARY		
	N-CHANNEL 1	N-CHANNEL 2
V_{DS} (V)	60	60
$R_{DS(on)}$ (Ω) at V_{GS} = 10 V	0.0190	0.0085
$R_{DS(on)}$ (Ω) at V_{GS} = 4.5 V	0.0240	0.0115
I_D (A)	20	54
Configuration	Dual N	
Package	PowerPAK SO-8L Dual Asymmetric	

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)

PARAMETER		SYMBOL	N-CHANNEL 1	N-CHANNEL 2	UNIT
Drain-source voltage		V_{DS}	60	60	V
Gate-source voltage		V_{GS}	± 20		
Continuous drain current	T_C = 25 °C	I_D	20 [a]	54	A
	T_C = 125 °C		15	31	
Continuous source current (diode conduction)		I_S	20 [a]	44	
Pulsed drain current [b]		I_{DM}	60	86	
Single pulse avalanche current	L = 0.1 mH	I_{AS}	18	30	
Single pulse avalanche energy		E_{AS}	16.2	45	mJ
Maximum power dissipation [b]	T_C = 25 °C	P_D	27	48	W
	T_C = 125 °C		9	16	
Operating junction and storage temperature range		T_J, T_{stg}	-55 to +175		°C
Soldering recommendations (peak temperature) [d, e]			260		

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	N-CHANNEL 1	N-CHANNEL 2	UNIT
Junction-to-ambient	PCB mount [c]	R_{thJA}	85	85	°C/W
Junction-to-case (drain)		R_{thJC}	5.5	3.1	

Notes

a. Package limited
b. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %
c. When mounted on 1" square PCB (FR4 material)
d. See solder profile (www.vishay.com/doc?73257). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components

SPECIFICATIONS (T_C = 25 °C, unless otherwise noted)								
PARAMETER	SYMBOL	TEST CONDITIONS			MIN.	TYP.	MAX.	UNIT
Static								
Drain-source breakdown voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 μA		N-Ch 1	60	-	-	V
		V_{GS} = 0 V, I_D = 250 μA		N-Ch 2	60	-	-	
Gate-source threshold voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 μA		N-Ch 1	1.5	2.0	2.5	
		V_{DS} = V_{GS}, I_D = 250 μA		N-Ch 2	1.5	2.0	2.5	
Gate-source leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V		N-Ch 1	-	-	± 100	nA
				N-Ch 2	-	-	± 100	
Zero gate voltage drain current	I_{DSS}	V_{GS} = 0 V	V_{DS} = 60 V	N-Ch 1	-	-	1	μA
		V_{GS} = 0 V	V_{DS} = 60 V	N-Ch 2	-	-	1	
		V_{GS} = 0 V	V_{DS} = 60 V, T_J = 125 °C	N-Ch 1	-	-	50	
		V_{GS} = 0 V	V_{DS} = 60 V, T_J = 125 °C	N-Ch 2	-	-	50	
		V_{GS} = 0 V	V_{DS} = 60 V, T_J = 175 °C	N-Ch 1	-	-	250	
		V_{GS} = 0 V	V_{DS} = 60 V, T_J = 175 °C	N-Ch 2	-	-	250	
On-state drain current [a]	$I_{D(on)}$	V_{GS} = 10 V	$V_{DS} \geq$ 5 V	N-Ch 1	15	-	-	A
		V_{GS} = 10 V	$V_{DS} \geq$ 5 V	N-Ch 2	30	-	-	
Drain-source on-state resistance [a]	$R_{DS(on)}$	V_{GS} = 10 V	I_D = 6 A	N-Ch 1	-	0.0155	0.0190	Ω
		V_{GS} = 10 V	I_D = 10 A	N-Ch 2	-	0.0070	0.0085	
		V_{GS} = 10 V	I_D = 6 A, T_J = 125 °C	N-Ch 1	-	-	0.0301	
		V_{GS} = 10 V	I_D = 10 A, T_J = 125 °C	N-Ch 2	-	-	0.0131	
		V_{GS} = 10 V	I_D = 6 A, T_J = 175 °C	N-Ch 1	-	-	0.0366	
		V_{GS} = 10 V	I_D = 10 A, T_J = 175 °C	N-Ch 2	-	-	0.0160	
		V_{GS} = 4.5 V	I_D = 4 A	N-Ch 1	-	0.0200	0.0240	
		V_{GS} = 4.5 V	I_D = 8 A	N-Ch 2	-	0.0094	0.0115	
Forward transconductance [b]	g_{fs}	V_{DS} = 10 V, I_D = 6 A		N-Ch 1	-	26	-	S
		V_{DS} = 10 V, I_D = 10 A		N-Ch 2	-	49	-	
Dynamic [b]								
Input capacitance	C_{iss}	V_{GS} = 0 V	V_{DS} = 25 V, f = 1 MHz	N-Ch 1	-	805	1100	pF
		V_{GS} = 0 V	V_{DS} = 25 V, f = 1 MHz	N-Ch 2	-	1790	2500	
Output capacitance	C_{oss}	V_{GS} = 0 V	V_{DS} = 25 V, f = 1 MHz	N-Ch 1	-	355	500	
		V_{GS} = 0 V	V_{DS} = 25 V, f = 1 MHz	N-Ch 2	-	800	1100	
Reverse transfer capacitance	C_{rss}	V_{GS} = 0 V	V_{DS} = 25 V, f = 1 MHz	N-Ch 1	-	13	20	
		V_{GS} = 0 V	V_{DS} = 25 V, f = 1 MHz	N-Ch 2	-	32	45	
Total gate charge [c]	Q_g	V_{GS} = 10 V	V_{DS} = 30 V, I_D = 1.5 A	N-Ch 1	-	12	20	nC
		V_{GS} = 10 V	V_{DS} = 30 V, I_D = 3 A	N-Ch 2	-	25	40	
Gate-source charge [c]	Q_{gs}	V_{GS} = 10 V	V_{DS} = 30 V, I_D = 1.5 A	N-Ch 1	-	2.6	-	
		V_{GS} = 10 V	V_{DS} = 30 V, I_D = 3 A	N-Ch 2	-	5.4	-	
Gate-drain charge [c]	Q_{gd}	V_{GS} = 10 V	V_{DS} = 30 V, I_D = 1.5 A	N-Ch 1	-	1.5	-	
		V_{GS} = 10 V	V_{DS} = 30 V, I_D = 3 A	N-Ch 2	-	3	-	
Gate resistance	R_g	f = 1 MHz		N-Ch 1	0.45	0.92	1.4	Ω
				N-Ch 2	0.2	0.46	0.7	

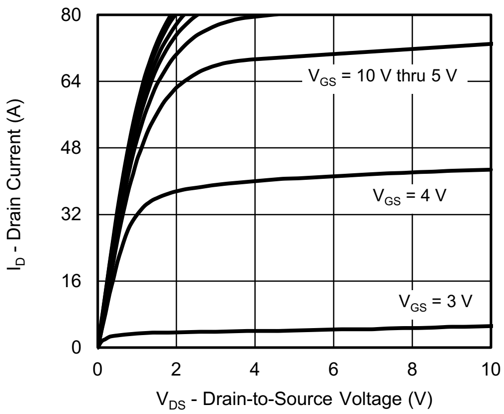
SPECIFICATIONS (T_C = 25 °C, unless otherwise noted)							
PARAMETER	**SYMBOL**	**TEST CONDITIONS**		**MIN.**	**TYP.**	**MAX.**	**UNIT**
Dynamic [b]							
Turn-on delay time [c]	$t_{d(on)}$	V_{DD} = 30 V, R_L = 20 Ω, $I_D \cong$ 1.5 A, V_{GEN} = 10 V, R_g = 1 Ω	N-Ch 1	-	10	15	ns
		V_{DD} = 30 V, R_L = 10 Ω, $I_D \cong$ 3 A, V_{GEN} = 10 V, R_g = 1 Ω	N-Ch 2	-	14	25	
Rise time [c]	t_r	V_{DD} = 30 V, R_L = 20 Ω, $I_D \cong$ 1.5 A, V_{GEN} = 10 V, R_g = 1 Ω	N-Ch 1	-	2	5	
		V_{DD} = 30 V, R_L = 10 Ω, $I_D \cong$ 3 A, V_{GEN} = 10 V, R_g = 1 Ω	N-Ch 2	-	3	5	
Turn-off delay time [c]	$t_{d(off)}$	V_{DD} = 30 V, R_L = 20 Ω, $I_D \cong$ 1.5 A, V_{GEN} = 10 V, R_g = 1 Ω	N-Ch 1	-	18	30	
		V_{DD} = 30 V, R_L = 10 Ω, $I_D \cong$ 3 A, V_{GEN} = 10 V, R_g = 1 Ω	N-Ch 2	-	26	40	
Fall time [c]	t_f	V_{DD} = 30 V, R_L = 20 Ω, $I_D \cong$ 1.5 A, V_{GEN} = 10 V, R_g = 1 Ω	N-Ch 1	-	10	15	
		V_{DD} = 30 V, R_L = 10 Ω, $I_D \cong$ 3 A, V_{GEN} = 10 V, R_g = 1 Ω	N-Ch 2	-	11	18	
Source-Drain Diode Ratings and Characteristics [b]							
Pulsed current [a]	I_{SM}		N-Ch 1	-	-	60	A
			N-Ch 2	-	-	86	
Forward voltage	V_{SD}	I_F = 6 A, V_{GS} = 0 V	N-Ch 1	-	0.83	1.2	V
		I_F = 10 A, V_{GS} = 0 V	N-Ch 2	-	0.82	1.2	
Body diode reverse recovery time	t_{rr}	I_F = 4 A, di/dt = 100 A/µs	N-Ch 1	-	31	65	ns
		I_F = 5 A, di/dt = 100 A/µs	N-Ch 2	-	47	100	
Body diode reverse recovery charge	Q_{rr}	I_F = 4 A, di/dt = 100 A/µs	N-Ch 1	-	26	55	nC
		I_F = 5 A, di/dt = 100 A/µs	N-Ch 2	-	55	110	
Reverse recovery fall time	t_a	I_F = 4 A, di/dt = 100 A/µs	N-Ch 1	-	16	-	ns
		I_F = 5 A, di/dt = 100 A/µs	N-Ch 2	-	24	-	
Reverse recovery rise time	t_b	I_F = 4 A, di/dt = 100 A/µs	N-Ch 1	-	15	-	
		I_F = 5 A, di/dt = 100 A/µs	N-Ch 2	-	23	-	
Body diode peak reverse recovery current	$I_{RM(REC)}$	I_F = 4 A, di/dt = 100 A/µs	N-Ch 1	-	-1.6	-	A
		I_F = 5 A, di/dt = 100 A/µs	N-Ch 2	-	-2.1	-	

Notes

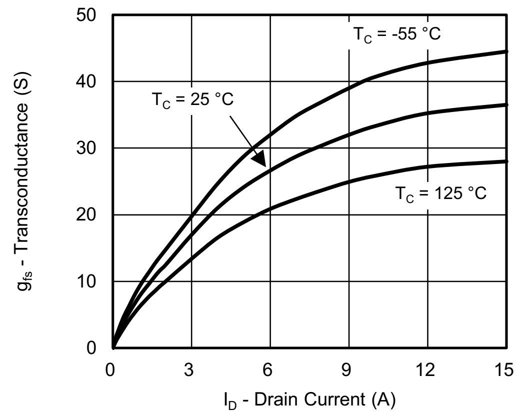
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %
b. Guaranteed by design, not subject to production testing
c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

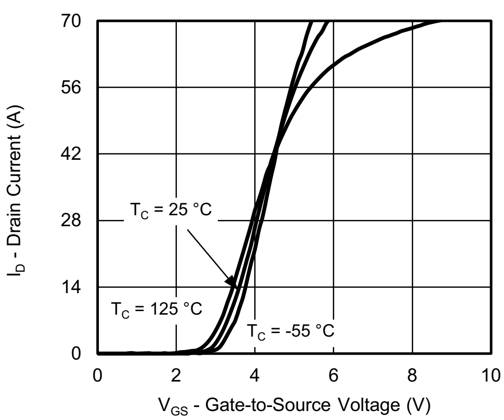
N-CHANNEL 1 TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



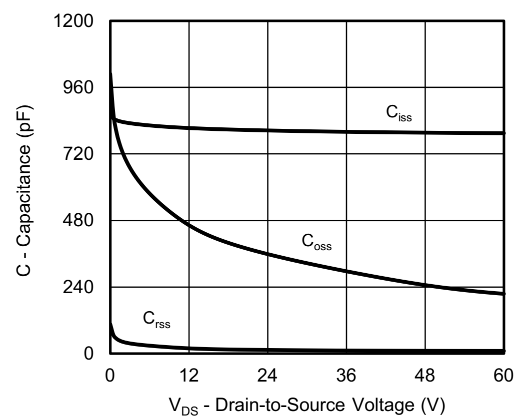
Output Characteristics



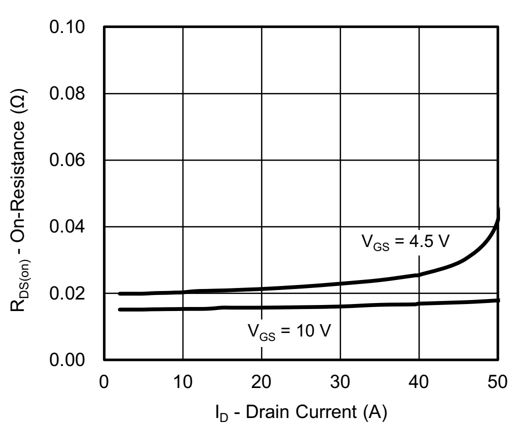
Transconductance



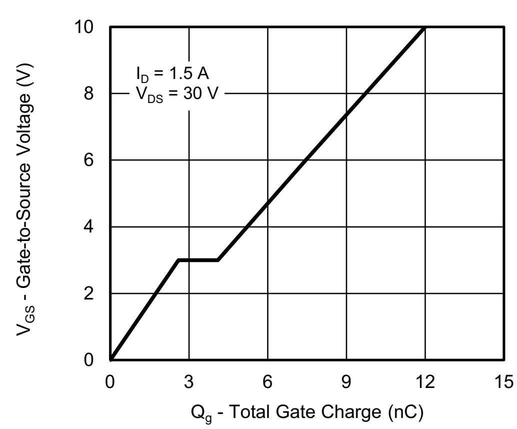
Transfer Characteristics



Capacitance

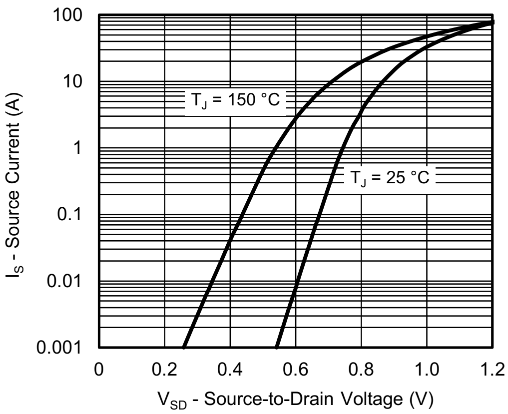


On-Resistance vs. Drain Current

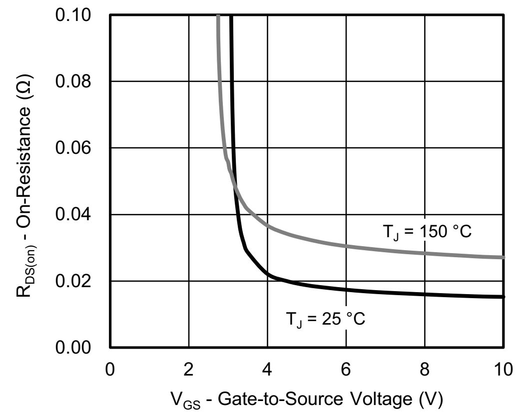


Gate Charge

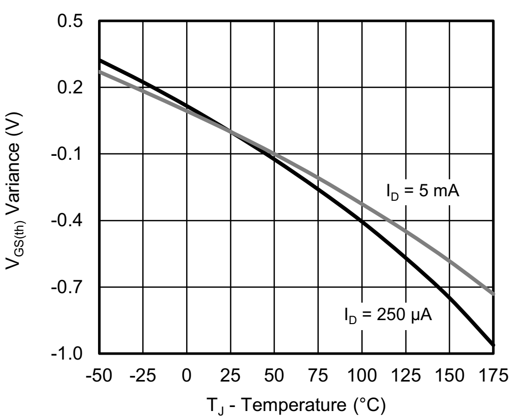
N-CHANNEL 1 TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



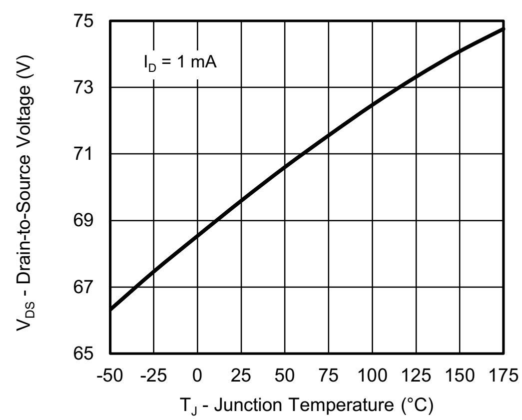
Source Drain Diode Forward Voltage



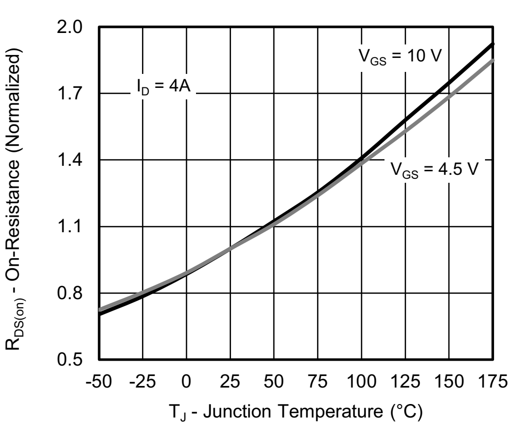
On-Resistance vs. Gate-to-Source Voltage



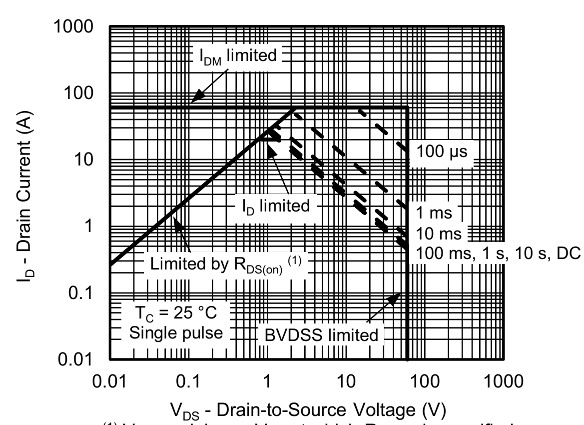
Threshold Voltage



Drain Source Breakdown vs. Junction Temperature



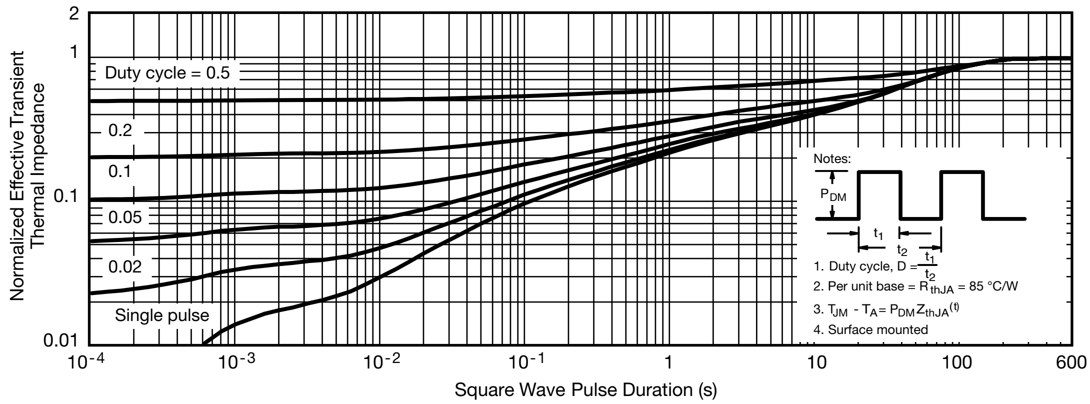
On-Resistance vs. Junction Temperature



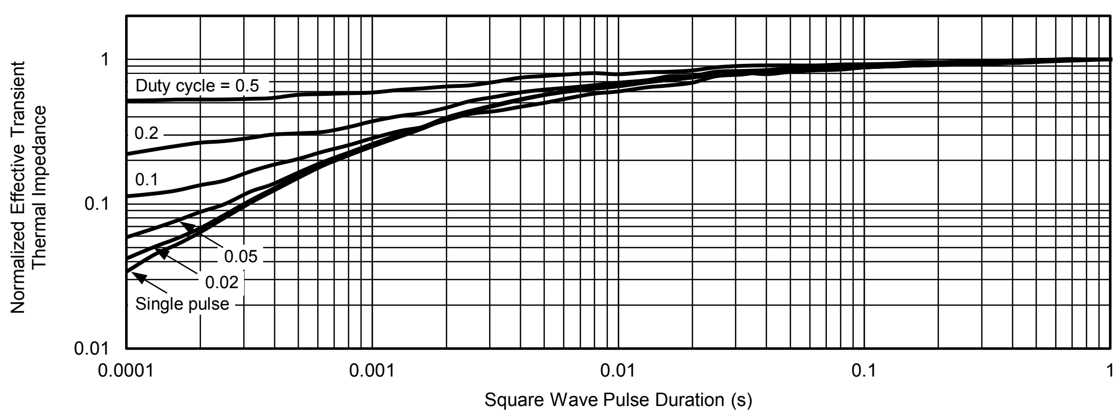
(1) V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area

N-CHANNEL 1 TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

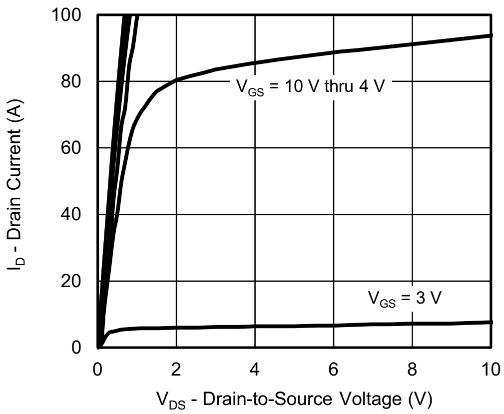


Normalized Thermal Transient Impedance, Junction-to-Case

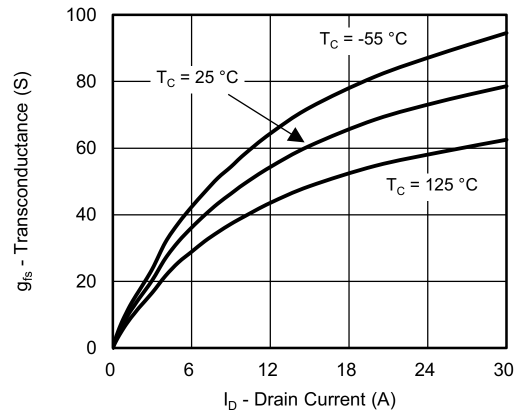
Note

- The characteristics shown in the graph:
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  is given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

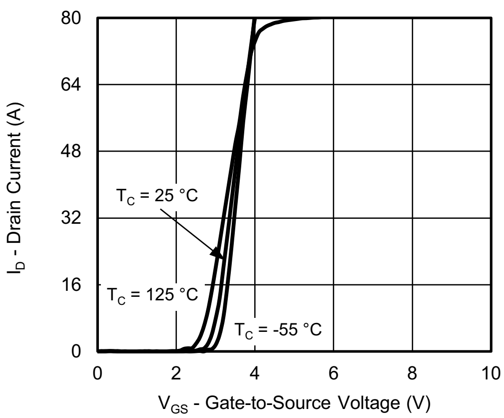
N-CHANNEL 2 TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



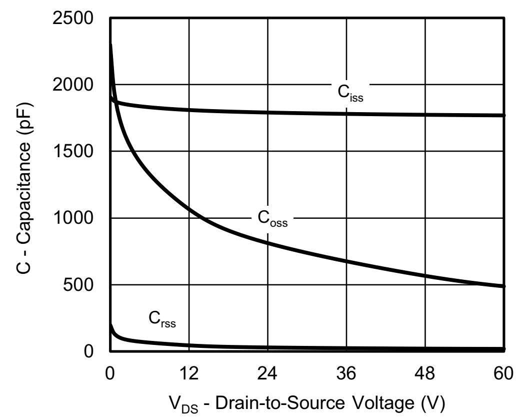
Output Characteristics



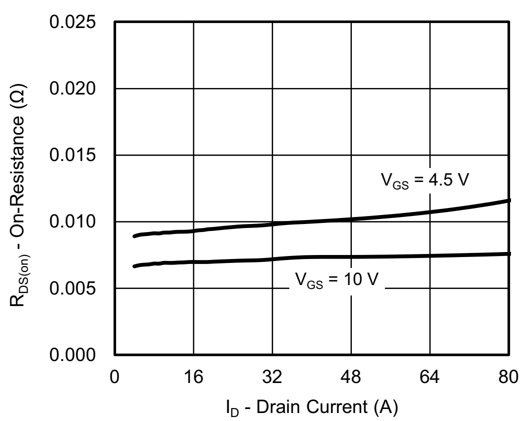
Transconductance



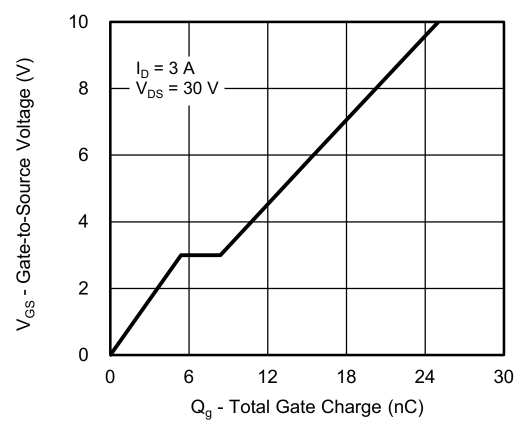
Transfer Characteristics



Capacitance



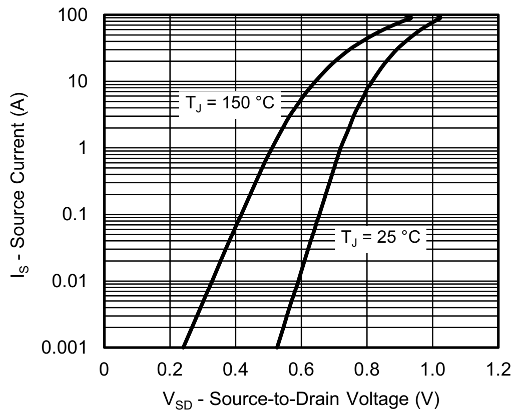
On-Resistance vs. Drain Current



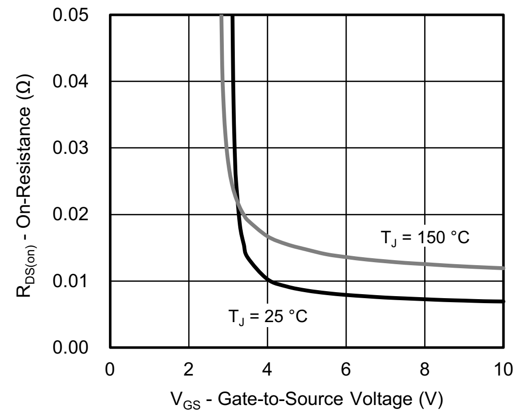
Gate Charge

For technical questions, contact: automostechsupport@vishay.com

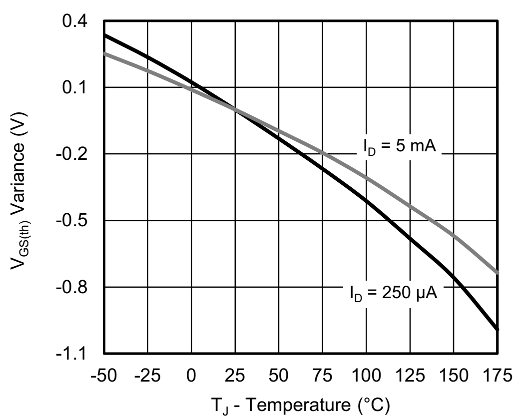
N-CHANNEL 2 TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



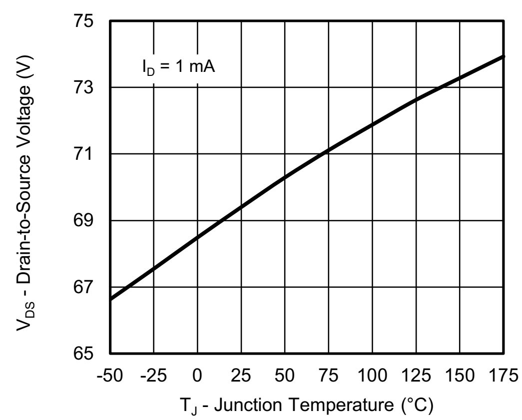
Source Drain Diode Forward Voltage



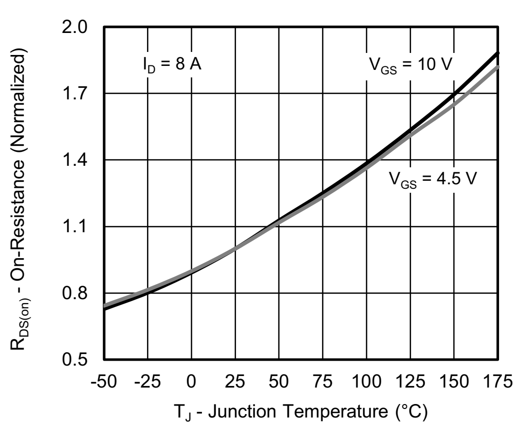
On-Resistance vs. Gate-to-Source Voltage



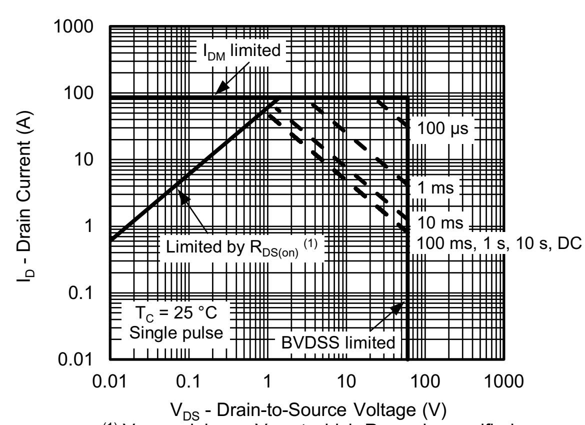
Threshold Voltage



Drain Source Breakdown vs. Junction Temperature



On-Resistance vs. Junction Temperature



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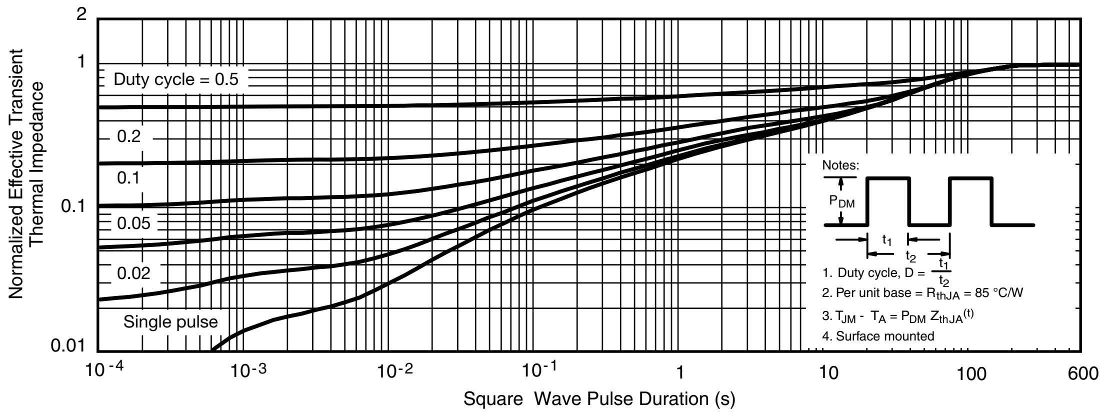
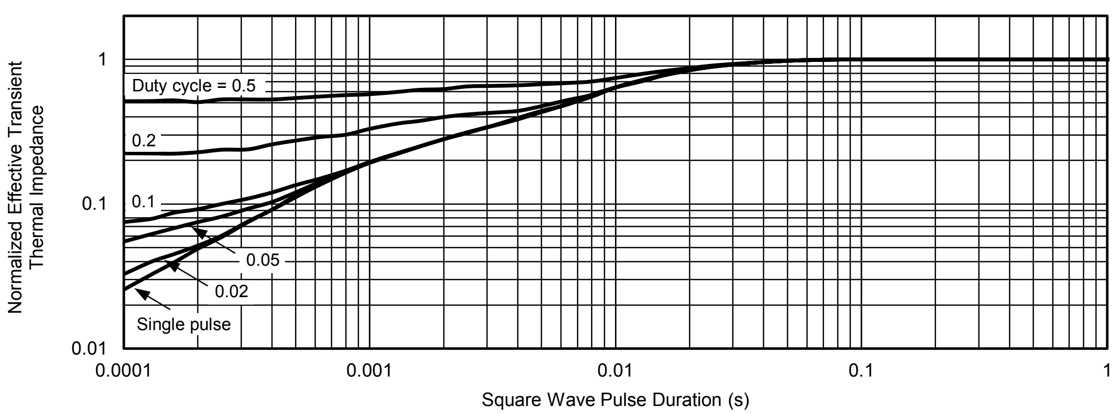
Safe Operating Area

N-CHANNEL 2 TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Note

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